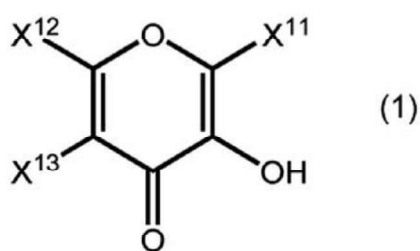


ABSTRACT

A polishing liquid for CMP, containing: abrasive grains; an additive; and water, in which the abrasive grains include cerium-based particles, the additive includes (A1) a 4-pyrone-based compound represented by General Formula (1) below and (B) a saturated monocarboxylic acid, and a pH is more than 4.0. A polishing liquid for CMP, containing: abrasive grains; an additive; and water, in which the abrasive grains include cerium-based particles, the additive includes (A2) picolinic acid and (B) a saturated monocarboxylic acid, and a pH is more than 4.0.

[Chemical Formula 1]



[in the formula, X^{11} , X^{12} , and X^{13} are each independently a hydrogen atom or a monovalent substituent.]

No Suitable Figure